

CORRECTION

High-Performance Dopamine Sensors Based on Whole-Graphene Solution-Gated Transistors

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The authors regret that an older version of Figure 4 was published. The correct Figure 4 is shown here:

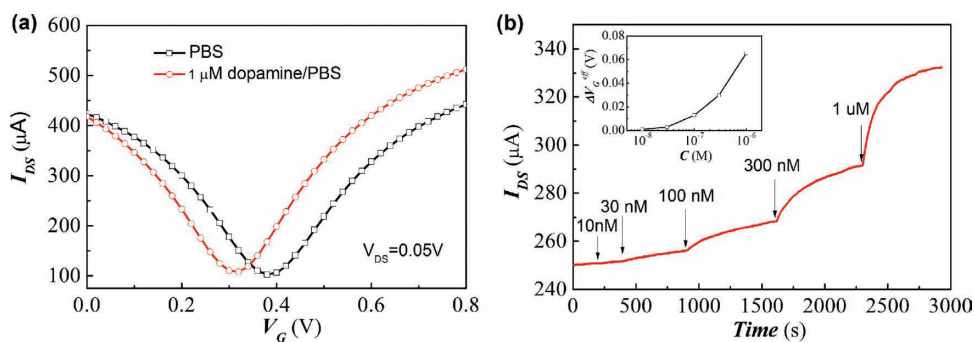


Figure 4. a) Transfer characteristics ($V_{DS} = 0.05$ V) of a SGGT with Pt gate electrode measured in PBS solution before and after the addition of dopamine with the concentration of 1 μ M. b) Channel current response of the SGGT to additions of dopamine with different concentrations. $V_{DS} = 0.05$ V, $V_G = 0.7$ V. Inset: the change of effective gate voltage (ΔV_G^{eff}) for different dopamine concentrations.